National Semiconductor Corporation

PRELIMINARY

LH0032/LH0032A/LH0032C/LH0032AC Ultra Fast FET-Input Operational Amplifier

General Description

The LH0032/LH0032A is a high slew rate, high input impedance differential operational amplifier suitable for diverse application in fast signal handling. The high allowable differential input voltage, ease of output clamping, and high output drive capability particularly suit it for comparator applications. It may be used in applications normally reserved for video amplifiers allowing the use of operational gain setting and frequency response shaping into the megahertz region.

The LH0032's wide bandwidth, high input impedance and high output capacity make it an ideal choice for applications such as summing amplifiers in high speed D to A converters, buffers in data acquisition systems and sample and hold circuits. Additional applications include high speed integrators and video amplifiers. The LH0032 and LH0032A are guaranteed for operation over the temperature range -55° C to $+125^{\circ}$ C, the LH0032C and LH0032AC are guaranteed for -25° C to $+85^{\circ}$ C.

Features

- 500 V/µs slew rate
- 70 MHz bandwidth
- $10^{12}\Omega$ input impedance
- As low as 2 mV max input offset voltage
- FET input
- Offset null with single pot
- No compensation for gains above 50
- Peak output current to 100 mA



Absolute Maximum Ratings

Supply Voltage, V	's	±18V
Input Voltage, V _{IN}	1	±Vs
Differential Input	Voltage	\pm 30V or \pm 2V _S
Power Dissipation	n, P _D	
T _A = 25°C	1.5W, derate	100°C/W to 125°C (Note 1)
T _C = 25℃	2.2W, derate	70°C/W to 125°C (Note 1)

Operating Temperature Range, T _A	
LH0032G/AG/E	-55°C to +125°C
LH0032CG/ACG	-25°C to +85°C
Operating Junction Temperature, T_J	175°C
Storage Temperature Range	-65°C to +150°C
Lead Temp. (Soldering, 10 seconds)	300°C

LH0032/LH0032A/LH0032C/LH0032AC

DC Electrical Characteristics $V_S = \pm 15V$, $T_{MIN} \le T_A \le T_{MAX}$ unless otherwise noted (Note 2) ($T_A = T_j$)

Oumbell Demonstern	Test Conditions		LH0032A		LH0032AC			LH0032			LH0032C					
Symbol Parameter			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Units	
V _{OS}	Input Offset Voltage		$T_A = T_J = 25^{\circ}C$ (Note 3)		1	2 5		2	5 7		2	5 10		2	15 20	m∨
ΔV _{OS} / ΔT	Average Offset Voltage Drift		(Note 4)		15	30		15	30		15	50		15	50	μV/⁰C
los	Input Offset Current	V _{IN} =0	$T_J = 25^{\circ}C$ (Note 3) $T_A = 25^{\circ}C$ (Note 5)			10 250 10			30 500 3			25 250 25			50 500 5	pA pA nA
IB	Input Bias Current		$T_J = 25^{\circ}C$ (Note 3) $T_A = 25^{\circ}C$ (Note 5)			50 1 25			150 5 10			100 1 50			500 5 15	pA nA nA
*VINCM	Input Voltage Range			±10	±12		±10	±12		±10	±12		±10	±12		v
CMRR	Common Mode Rejection Ratio	$\Delta V_{IN} = \pm 10V$		50	60		50	60		50	60		50	60		dB
AVOL	Open-Loop Voltage	V _O = ±10V, f=1 kHz	T _J =25°C	60	70		60	70		60	70		60	70		dB
	Gain	$R_L = 1 k\Omega$ (Note 6)		57			57			57			57			
Vo	Output Voltage Swing	$R_L = 1 k\Omega$		±10	±13.5		±10	±13		±10	±13.5		±10	±13		v
Is	Power Supply Current	T _A =25°C, I _O =0 (Note 5)			18	20		20	22		18	20		20	22	mA
PSRR	Power Supply Rejection Ratio	$\Delta V_S = 10V$ (±5 to ±15V)		50	60		50	60		50	60		50	60		dB

AC Electrical Characteristics $V_S = \pm 15V$, $R_L = 1k\Omega$, $T_J = 25^{\circ}C$ (Note 7)

Symbol	Parameter	Con	Min	Тур	Max	Units	
SR	Slew Rate	$A_V = +1$		350	500		V/µs
ts	Settling Time to 1% of Final Value	$A_{V} = -1$,	$\Delta V_{IN} = 20V$		100		
ts	Settling Time to 0.1% of Final Value] ^v - ',	74IN - 204		300		ns
t _R	Small Signal Rise Time	$A_{V} = +1, \Delta V_{\rm IN} = 1V$			8	20	
tD	Small Signal Delay Time				10	25	

Note 1. In order to limit maximum junction temperature to +175°C, it may be necessary to operate with VS $\leq \pm 15V$ when T_A or T_C exceeds specific values depending on the P_D within the device package. Total P_D is the sum of quiescent and load-related dissipation. See applications notes AN-277, "Applications of Wide-Band Buffer Amplifiers" and AN-253, "High-Speed Operational-Amplifier Applications" for a discussion of toad-related power dissipation.

Note 2. LH0032AG/G are 100% production tested as specified at 25°C, 125°C, and -55°C. LH0032ACG/CG are 100% production tested at 25°C only. Specifications at temperature extremes are verified by sample testing, but these limits are not used to calculate outgoing quality level.

Note 3. Specification is at 25°C junction temperature due to requirements of high-speed automatic testing. Actual values at operating temperature will exceed the value at $T_J = 25$ C. When supply voltages are \pm 15V, no-load operating junction temperature may rise 40–60°C above ambient, and more under load conditions. Accordingly, V_{QS} may change one to several mV, and I_B and I_{QS} will change significantly during warm-up. Refer to I_B and I_{QS} vs. temperature graph for expected values.

Note 4. LH0032AG/G are 100% production tested for this parameter. LH0032ACG/CG are sample tested only. Limits are not used to calculate outgoing quality levels. $\Delta V_{OS}/\Delta T$ is the average value calculated from measurements at 25°C and T_{MAX}.

Note 5. Measured in still air 7 minutes after application of power. Guaranteed thru correlated automatic pulse testing.

Note 6. Guaranteed thru correlated automatic pulse testing at $T_J \approx 25^{\circ}C$.

Note 7. Not 100% production tested; verified by sample testing only. Limits are not used to calculate outgoing quality level. *Guaranteed by CMRR test condition.

Connection Diagrams







See NS Package Number E48B

Auxiliary Circuits



TL/K/5265-15

Output Short Circuit Protection



TL/K/5265-16

Typical Performance Characteristics Maximum Power Supply Current vs. Input Voltage Range and Output Dissipation Supply Voltage Voltage vs. Supply Voltage 2.5 24 20 INFINITE HEAT SINK $R_1 = 1k$ -55°C TA = 22 Tc = 25°C 2.0 POWER DISSIPATION (W) SUPPLY CURRENT (mA) 15 20 VINCM. VOUT (±V) HJC = 70°C/W Tc = 25 1.5 'n Vour 18 10 16 1.0 VIN NO HEAT SINK 14 + 125°C 5 θ_JA = 100°C/W Ta = 0.5 12 0 10 0 125 100 150 0 25 50 75 5 10 15 20 n 5 10 15 20 TEMPERATURE (°C) SUPPLY VOLTAGE (± V) SUPPLY VOLTAGE (± V) **Bode Plot Bode Plot (Unity Gain** Large Signal Frequency (Uncompensated) Compensation) Response 80 26 80 $V_S = \pm 15V$ 11110 ٧s = ± 15V 24 22 60 OUTPUT SWING (Vp-p) 60 **VOLTAGE GAIN (dB)** 20 **/OLTAGE GAIN (dB)** PHASE (DEGREES PHASE (DEGREES) 90 18 PHASE 135 40 40 45 16 14 180 90 ± 15V Vs GAIN 12 225 R = 16 135 20 20 10 . 25 270 8 6 n n 1M 10M 100M 10 100 1.M 101 100M 100M 10k 100k 10k 100 1M 10M FREQUENCY (Hz) FREQUENCY (Hz) FREQUENCY (Hz) **Common Mode Rejection** Large Signal Pulse Large Signal Puise Ratio vs. Frequency Response Response 90 COMMON-MODE REJECTION RATIO (dB) +10 10 80 - 18 ٧s ± 15 $V_S = \pm 15V$ Ay = +170 Av = +10OUTPUT VOLTAGE (V) OUTPUT VOLTAGE (V) +5 5 R = 1% $\mathbf{R}_{i} = \mathbf{1}\mathbf{k}$ 60 50 0 0 40 30 -5 - 5 20 10 -10 -10 n 100k 1M 10M 100M 100 200 300 400 500 0 100 200 300 400 500 10k 0 FREQUENCY (Hz) TIME (ns) TIME (ns) Normalized Input Bias and Offset **Normalized Input Bias Total Input Noise** Voltage vs. Frequency* Current vs. Junction Temperature Current During Warm-Up 104 100 120 INPUT NOISE VOLTAGE (nV/ JHZ) 110 $V_S = \pm 15V$ 100 CURRENT—NORMALIZED TO CURRENT AT TIME = 0 CURRENT—NORMALIZED TO CURRENT AT $T_J = 25^{\circ}C$ 10³ TA = 25°C 90 80 70 102 10 60 RS 50 40 10¹ 30 20 **FOTAL I** 10 100 ۵ 25 45 65 85 105 125 145 165 0 2 4 6 8 10 10 100 1 k 101 JUNCTION TEMPERATURE (°C) TIME FROM POWER TURN-ON (MINUTES) FREQUENCY (Hz) TL/K/5265-2

*Noise voltage includes contribution from source resistance.

Typical Applications







TL/K/5265-19



TL/K/5265-18





TL/K/5265-20



Applications Information

POWER SUPPLY DECOUPLING

The LH0032/LH0032A, like most high speed circuits, is sensitive to layout and stray capacitance. Power supplies should be by passed as near to pins 10 and 12 as practicable with low inductance capacitors such as 0.01 μF disc ceramics. Compensation components should also be located close to the appropriate pins to minimize stray reactances.

INPUT CURRENT

Because the input devices are FETs, the input bias current may be expected to double for each 11°C junction temperature rise. This characteristic is plotted in the typical performance characteristics graphs. The device will self-heat due to internal power dissipation after application of power thus raising the FET junction temperature $40-60^{\circ}$ C above free-air ambient temperature when supplies are \pm 15V. The de-

Applications Information (Continued)

vice temperature will stabilize within 5–10 minutes after application of power, and the input bias currents measured at that time will be indicative of normal operating currents. An additional rise would occur as power is delivered to a load due to additional internal power dissipation.

There is an additional effect on input bias current as the input voltage is changed. The effect, common to all FETs, is an avalanche-like increase in gate current as the FET gate-to-drain voltage is increased above a critical value depending on FET geometry and doping levels. This effect will be noted as the input voltage of the LH0032 is taken below ground potential when the supplies are \pm 15V. All of the effects described here may be minimized by operating the device with V_S \leq ± 15V.

These effects are indicated in the typical performance curves.

INPUT CAPACITANCE

The input capacitance to the LH0032/LH0032C is typically 5pF and thus may form a significant time constant with high value resistors. For optimum performance, the input capacitance to the inverting input should be compensated by a small capacitor across the feedback resistor. The value is strongly dependent on layout and closed loop gain, but will typically be in the neighborhood of several picofarads.

In the non-inverting configuration, it may be advantageous to bootstrap the case and/or a guard conductor to the inverting input. This serves both to divert leakage currents away from the non-inverting input and to reduce the effective input capacitance. A unity gain follower so treated will have an input capacitance under a picotarad.

HEAT SINKING

While the LH0032/LH0032A is specified for operation without any explicit heat sink, internal power dissipation does cause a significant temperature rise. Improved bias current performance can thus be obtained by limiting this temperature rise with a small heat sink such as the Thermalloy No. 2241 or equivalent. The case of the device has no internal connection, so it may be electrically connected to the sink if this is advantageous. Be aware, however, that this will affect the stray capacitances to all pins and may thus require adjustment of circuit compensation values.

For additional applications information request Application Note AN-253.